TOSHIBA TC75S58F/FU

TOSHIBA CMOS LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

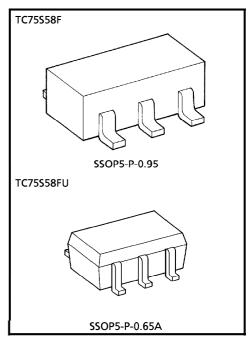
TC75S58F, TC75S58FU

SINGLE COMPARATOR

TC75S58F, TC75S58FU are CMOS type general-purpose single comparator capable of single power supply operation and using lower supply currents than the conventional bipolar comparators. Its open drain output forms wired OR with other open drain outputs.

FEATURES

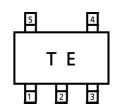
- Low supply current : IDD = 10μ A (Typ.)
- Single power supply operation
- Wide common mode input voltage range: VSS~VDD-0.9V
- Open drain output circuit
- Low input bias current
- Small package



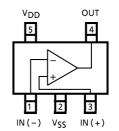
Weight

SSOP5-P-0.95 : 0.014g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

MARKING (TOP VIEW)



PIN CONNECTION (TOP VIEW)



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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{DD} , V _{SS}	±3.5 or 7	V
Differential Input Voltage	DVIN	± 7	V
Input Voltage	V _{IN}	$V_{SS} \sim V_{DD}$	V
Output Current	10	± 35	mA
Power Dissipation	PD	200	mW
Operating Temperature	T _{opr}	- 40∼85	°C
Storage Temperature	T _{stg}	- 55∼125	°C

(Note) Since this product sometimes brings about latchup, which is peculiar to CMOS devices, note the following points:

- Don't raise the voltage level of I/O pins beyond V_{DD}, nor lower it below V_{SS}. Consider the timing for power supply, too.
- Don't let any abnormal noise enter the device.

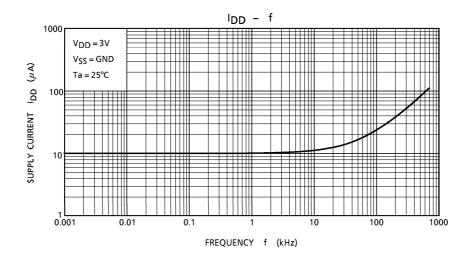
ELECTRICAL CHARACTERISTICS ($V_{DD} = 5V$, $V_{SS} = GND$, Ta = 25°C)

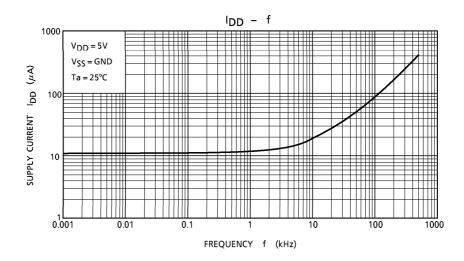
CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Offset Voltage	V _{IO}	_	_	_	± 1	± 7	mV
Input Offset Current	lo	_	_	_	1	_	pА
Input Bias Current	Ц	_	_	_	1	_	pА
Common Mode Input Voltage	CMVIN	_	_	0	_	4.1	٧
Supply Current	I _{DD} (Note)	_	-	_	11	22	μΑ
Voltage Gain	GV	_		_	94	_	dB
Sink Current	l _{sink}	_	V _{OL} = 0.5V	13	25	_	mA
Output Leak Current	ILEAK	_	V _O = 5V	_	5	_	nΑ
Output Voltage	VOL	_	I _{sink} = 5.0mA	_	0.1	0.3	V
Operating Supply Voltage	V _{DD}	_	_	1.8	_	7.0	٧
Propagation Delay	^t PLH (1)	_	Over drive = 100mV	_	800	_	ne
Time (Turn ON)	^t PLH (2)	_	TTL step input	_	620	_	ns
Propagation Delay	tPHL (1)	_	Over drive = 100mV	_	230	_	ns
Time (Turn OFF)	tPHL (2)	_	TTL step input	_	350	_	
Response Time	tTLH	_	Over drive = 100mV	_	190	_	ns
	tTHL		Over drive = 100mV	_	6	_	

ELECTRICAL CHARACTERISTICS ($V_{DD} = 3V$, $V_{SS} = GND$, Ta = 25°C)

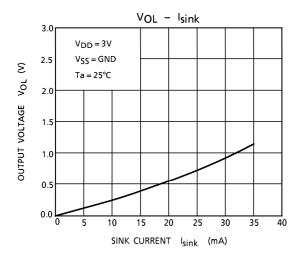
CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Offset Voltage	V _{IO}	_	_	_	± 1	±7	mV
Input Offset Current	lo	_	_	_	1	_	pА
Input Bias Current	Ц	_	_	_	1	_	pА
Common Mode Input Voltage	CMVIN	_	_	0	_	2.1	V
Supply Current	I _{DD} (Note)	_	_	_	10	20	μΑ
Sink Current	l _{sink}	_	V _{OL} = 0.5V	6	18	_	mA
Output Leak Current	ILEAK	_	V _O = 3V	_	5	_	nΑ
Output Voltage	VOL	_	l _{sink} = 5.0mA	_	0.15	0.35	٧
Propagation Delay Time (Turn ON)	t _{PLH}	_	Over drive = 100mV	_	590	_	ns
Propagation Delay Time (Turn OFF)	t _{PHL}	_	Over drive = 100mV	_	230	_	ns
Response Time	tTLH	_	Over drive = 100mV	_	170	_	nc
	tTHL		Over drive = 100mV	_	5	_	ns

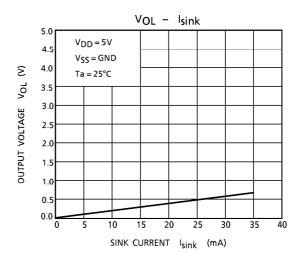
(Note) Since this product causes an increase in current consumption with a rise in operational frequency, make sure that power consumption does not exceed the allowable dissipation.

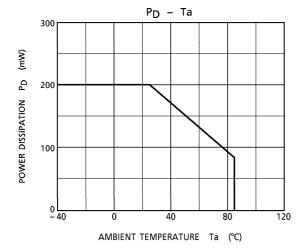




4/7

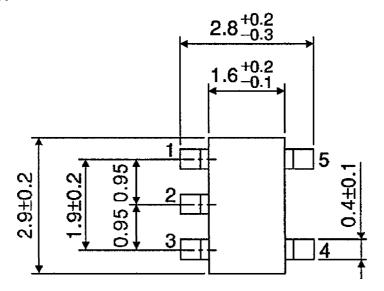


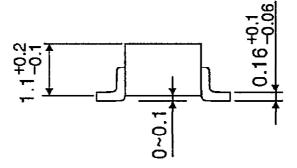




OUTLINE DRAWING SSOP5-P-0.95

Unit: mm

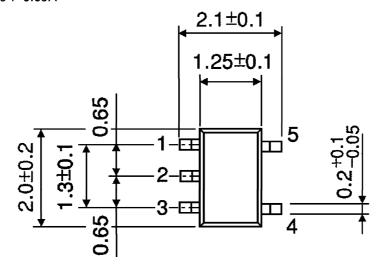


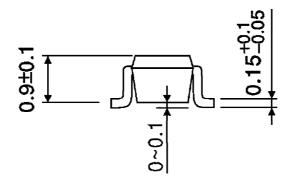


Weight: 0.014g (Typ.)

OUTLINE DRAWING SSOP5-P-0.65A

Unit: mm





Weight: 0.006g (Typ.)